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TABLE OF CONTENTS

Crystallization of Ion Amorphized Ge₂Sb₂Te₅ in Nano-structured Thin Films	1
<i>A. M. Mio, E. Carria, R. De Bastiani, M. Miritello, C. Bongiorno, G. D'Arrigo, C. Spinella, M. G. Grimaldi, E. Rimini</i>	
Crystallization Behavior of Ge₁Cu₂Te₃ Amorphous Film	7
<i>Y. Sutou, T. Kamada, Y. Saito, M. Sumiya, J. Koike</i>	
Stress Limited Scaling in Ge₂Sb₂Te₅	13
<i>Robert E. Simpson, Milos Krbal, Paul J. Fons, Alexander V. Kolobov, Tomoya Uruga, Hajime Tanida, Junji Tominaga</i>	
GeTe-filled Carbon Nanotubes for Data Storage Applications	19
<i>Cristina E. Giusca, Vlad Stolojan, Jeremy Sloan, Hidetsugu Shiozawa, S. Ravi P. Silva</i>	
Local Order and Crystallization of Laser Quenched and Ion Implanted Amorphous Ge_{1-x}Te_x Thin Films	25
<i>E. Carria, R. De Bastiani, S. Gibilisco, A. Mio, M. Miritello, A. R. Pennisi, C. Bongiorno, M. G. Grimaldi, E. Rimini</i>	
Studies of Ge-Sb-Te Phase Change Materials at and Above Melting Temperatures and Set to Reset Transition of Memory Devices	31
<i>Semyon D. Savransky, Guy Wicker</i>	
Study of Crystalline Structure N-doped GeSb Phase Change Material for PCRAM Applications	37
<i>A. Bastard, S. Lhostis, C. Bonafos, S. Schamm-Chardon, P. E. Coulon, F. Fillot, G. Ghezzi, A. Fantini, L. Perniola, S. Loubriat, A. Roule, E. Gourvest, E. Arbaoui, A. Fargeix, M. Armand, B. Hyot, S. Maitrejean, V. Sousa</i>	
Ab Initio Calculations of Crystalline and Amorphous In₂Se₃ Compounds for Chalcogenide Phase Change Memory	43
<i>Renyu Chen, Scott T. Dunham</i>	
Influence of Bottom Contact Material on the Selective Chemical Vapor Deposition of Crystalline GeSbTe Alloys	49
<i>Alejandro G. Schrott, Chieh-Fang Chen, Matthew J. Breitwisch, Eric A. Joseph, Ravi K. Dasaka, Roger W. Cheek, Yu Zhu, Chung Lam</i>	
Phase Transition Behaviors of AgInSbTe-SiO₂ Nanocomposite Thin Films for Phasechange Memory Applications	55
<i>Yu-Jen Huang, Tzu-Chin Chung, Chiung-Hsin Wang, Tsung-Eong Hsieh</i>	
Ce Doped-GeSbTe Thin Films Applied to Phase-Change Random Access Memory Devices	61
<i>Yu-Jen Huang, Min-Chuan Tsai, Chiung-Hsin Wang, Tsung-Eong Hsieh</i>	
Crystalline Path Formation in Nanoglasses of PCM	67
<i>M. Nardone, M. Simon, I. V. Karpov, V. G. Karpov</i>	

Activated Pulsed Metalorganic Chemical Vapor Deposition of Ge₂Sb₂Te₅ Thin Films Using Alkyl Precursors	74
<i>Denis Reso, Mindaugas Silinskas, Bodo Kalkofen, Marco Lisker, Edmund P. Burte</i>	
The Role of Vacancies in the Pressure Amorphisation Phenomenon Observed in Ge-Sb-Te Phase Change Alloys	80
<i>M. Krbal, A. V. Kolobov, P. Fons, J. Tominaga, J. Haines, A. Pradel, M. Ribes, C. Levelut, R. Le Parc, M. Hanfland</i>	
Understanding Phase Change Memory Reliability and Scaling by Physical Models of the Amorphous Chalcogenide Phase	87
<i>Daniele Ielmini</i>	
Electrical Resistance Change with Crystallization in Si-Te Amorphous Thin Films	99
<i>Yuta Saito, Yuji Sutou, Junichi Koike</i>	
Amorphization of Crystalline Phase Change Material by Ion Implantation	105
<i>Simone Raoux, Guy M. Cohen, Robert M. Shelby, Huai-Yu Cheng, Jean L. Jordan Sweet</i>	
Charge Transport in Nanoglasses of Phase-Change Memory	111
<i>M. Simon, M. Nardone, S. A. Kostylev, I. V. Karpov, V. G. Karpov</i>	
Author Index	